Vishay Siliconix

## Automotive N-Channel 40 V (D-S) 175 °C MOSFET

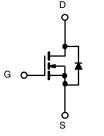
PRODUCT SUMMARY	
V <sub>DS</sub> (V)	40
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0017
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0020
I <sub>D</sub> (A)	200
Configuration	Single

# 

### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 8x8L
Lead (Pb)-free and Halogen-free	SQJQ402E-T1-GE3

ABSOLUTE MAXIMUM RATINGS	$T_C = 25  ^{\circ}C$ , unles	ss otherwise noted	)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	40	V
Gate-Source Voltage		$V_{GS}$	± 20	V
Outlier - Poils Outlie	T <sub>C</sub> = 25 °C a	1	200	
Continuous Drain Current	T <sub>C</sub> = 125 °C	l <sub>D</sub>	127	
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	200	Α
Pulsed Drain Current b		I <sub>DM</sub>	300	
Single Pulse Avalanche Current  L = 0.1 mH		I <sub>AS</sub>	85	
Single Pulse Avalanche Energy	L = 0.1 IIII	E <sub>AS</sub>	361	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	150	W
Maximum Fower Dissipation	T <sub>C</sub> = 125 °C		50	VV
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering Recommendations (Peak Temperature) d, e			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount c	$R_{thJA}$	50	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	1	C/VV

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300 \,\mu\text{s}$ , duty cycle  $\leq 2 \,\%$ .
- c. When mounted on 1" square Pcb (Fr4 material).
- d. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK 8x8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0$ , $I_D = 250 \mu A$		40	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2	2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	150			
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> ≥ 5 V	100	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.0013	0.0017	Ω	
Dunin Course On Chata Basistana 8	Б	V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 10 A	-	0.0015	0.0020		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0026		
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0031		
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		-	140	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 20 V, f = 1 MHz	-	10 760	13 500	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		=	1370	1800		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	650	850		
Total Gate Charge <sup>c</sup>	$Q_g$		V <sub>DS</sub> = 20 V, I <sub>D</sub> = 40 A	=.	169	260	nC	
Gate-Source Charge c	Q <sub>gs</sub>	$V_{GS} = 10 \text{ V}$		=	32	-		
Gate-Drain Charge c	$Q_{gd}$			=	29	-		
Gate Resistance	$R_g$	f = 1 MHz		0.6	1.3	2.5	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	19	30		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 0.5 $\Omega$ $I_D \cong$ 40 A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		=	15	25	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	69	110		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	11	20		
Source-Drain Diode Ratings and Cha	racteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	300	Α	
Forward Voltage	$V_{SD}$	1	= 50 A, V <sub>GS</sub> = 0		0.82	1.2	V	

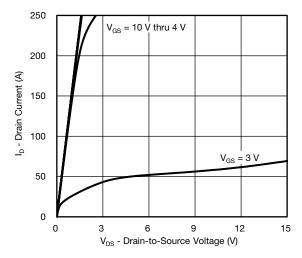
### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

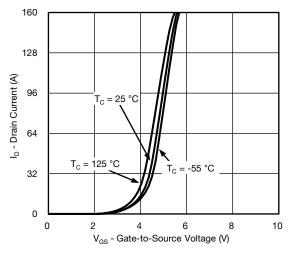
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



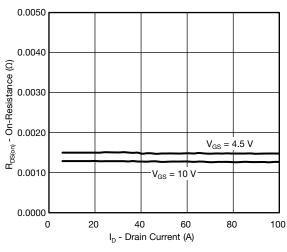
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



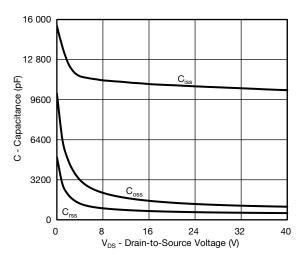
### **Output Characteristics**



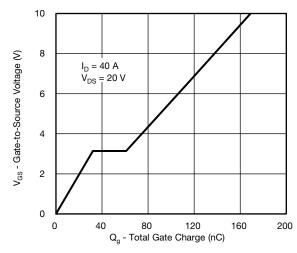
### **Transfer Characteristics**



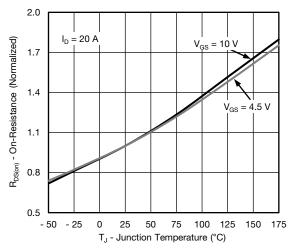
On-Resistance vs. Drain Current



#### Capacitance



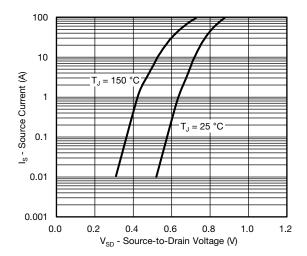
**Gate Charge** 



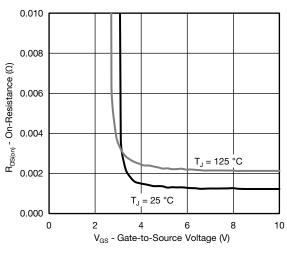
On-Resistance vs. Junction Temperature



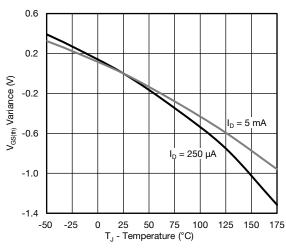
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



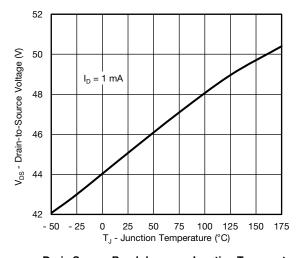
### **Source Drain Diode Forward Voltage**



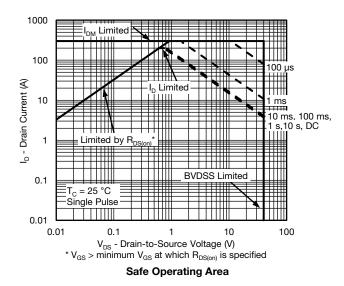
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 

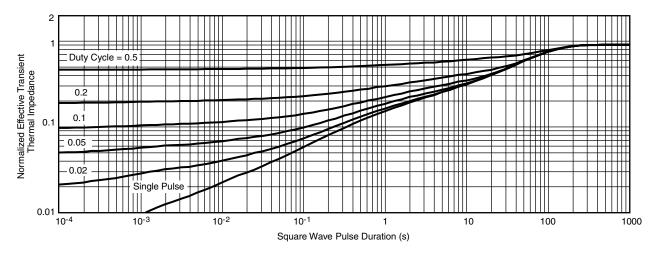


Drain Source Breakdown vs. Junction Temperature

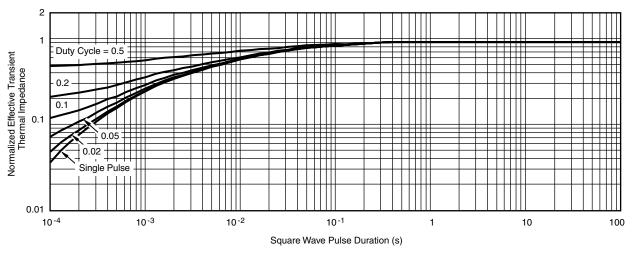




## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?62748">www.vishay.com/ppg?62748</a>.





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## PowerPAK® 8 x 8L

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK 8 x 8L package:

DATASHEET PART NUMBER	OLD ORDERING CODE a	NEW ORDERING CODE
SQJQ402E	SQJQ402E-T1-GE3	SQJQ402E-T1_GE3

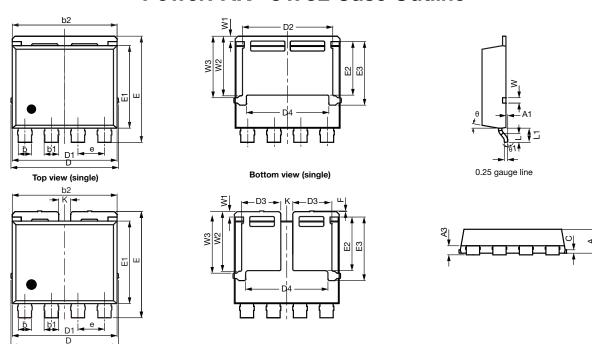
### Note

a. Old ordering code is obsolete and no longer valid for new orders



Top view (dual)

## PowerPAK® 8 x 8L Case Outline



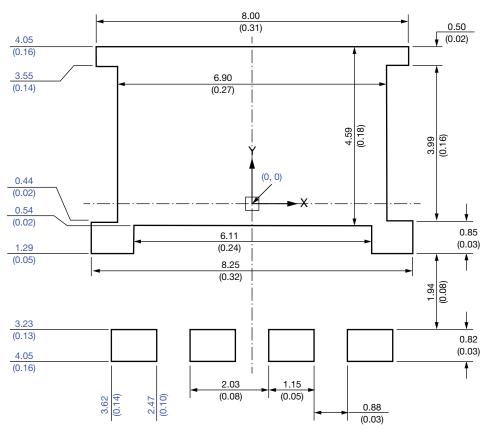
Bottom view (dual)

DIM		MILLIMETERS		INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	1.70	1.80	1.90	0.067	0.071	0.075
A1	0.00	0.08	0.13	0.000	0.003	0.005
A3	0.55	0.62	0.70	0.022	0.024	0.028
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	7.80	7.90	8.00	0.307	0.311	0.315
С	0.20	0.25	0.30	0.008	0.010	0.012
D	8.00	8.10	8.25	0.315	0.319	0.325
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D3	2.85	2.95	3.05	0.112	0.116	0.120
D4	6.11	6.21	6.31	0.241	0.244	0.248
е	1.95	2.00	2.05	0.077	0.079	0.081
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	3.94	4.04	4.14	0.140	0.159	0.163
E3	4.69	4.79	4.89	0.185	0.189	0.193
F	0.05	0.10	0.15	0.002	0.004	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.80	0.90	1.00	0.031	0.035	0.039
W	0.30	0.40	0.50	0.012	0.016	0.020
W1	0.30	0.40	0.50	0.012	0.016	0.020
W2	4.39	4.49	4.59	0.173	0.177	0.181
W3	4.54	4.64	4.74	0.179	0.183	0.187
θ	6°	10°	14°	6°	10°	14°
θ1	0°	3°	8°	0°	3°	8°
θ1 -0891-Rev. A, G: 6026	ŭ	3°	8°	0°	3°	

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## Recommended Minimum PADs for PowerPAK® 8 x 8L Single



### Dimensions in millimeters (inches)

### Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



## **Legal Disclaimer Notice**

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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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